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March 2013

FQP17P06 P-Channel QFET® MOSFET

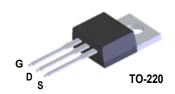
- 60 V, - 17 A, 120 $m\Omega$

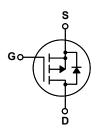
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- - 17 A, 60 V, $R_{DS(on)}$ = 120 m Ω (Max.) @ V_{GS} = 10 V, ID = 8.5 A
- Low Gate Charge (Typ.21 nC)
- Low Crss (Typ. 80 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

| Symbol | Parameter | | | FQP17P06 | Unit |
|-----------------------------------|---|-----------------------------------|----------|-------------|------|
| V_{DSS} | Drain-Source Voltage | | -60 | V | |
| I _D | Drain Current - Continuous (T _C = 25°C) | | °C) | -17 | Α |
| | | - Continuous (T _C = 10 | 0°C) | -12 | А |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | -68 | Α |
| V _{GSS} | Gate-Source Vo | oltage | | ± 25 | V |
| E _{AS} | Single Pulsed Avalanche Energy | | (Note 2) | 300 | mJ |
| I _{AR} | Avalanche Curr | Avalanche Current | | -17 | А |
| E _{AR} | Repetitive Avalanche Energy | | (Note 1) | 7.9 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | | (Note 3) | -7.0 | V/ns |
| P _D | Power Dissipation (T _C = 25°C) | | | 79 | W |
| | - Derate above 25°C | | | 0.53 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Range | | | -55 to +175 | °C |
| T _L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | | | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FQP17P06 | Unit |
|-----------------|---|----------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 1.9 | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink, Typ. | 0.5 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | °C/W |

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit |
|---|--|--|------|-------|------|------|
| Off Cha | aracteristics | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | -60 | | | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I_D = -250 μA, Referenced to 25°C | | -0.06 | | V/°C |
| I _{DSS} | 7 0 1 1/1 5 1 0 1 | V _{DS} = -60 V, V _{GS} = 0 V | | | -1 | μΑ |
| | Zero Gate Voltage Drain Current | V _{DS} = -48 V, T _C = 150°C | | | -10 | μА |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = -25 V, V _{DS} = 0 V | | | -100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse V _{GS} = 25 V, V _{DS} = 0 V | | | | 100 | nA |
| On Cha | racteristics | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = -250 μA | -2.0 | | -4.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = -10 V, I _D = -8.5 A | | 0.094 | 0.12 | Ω |
| 9 _{FS} | Forward Transconductance $V_{DS} = -30 \text{ V}, I_D = -8.5 \text{ A}$ | | | 9.3 | | S |
| Dynam | ic Characteristics | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = -25 V, V _{GS} = 0 V, | | 690 | 900 | pF |
| C _{oss} | Output Capacitance | f = 1.0 MHz | | 325 | 420 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 80 | 105 | pF |
| Switchi | ing Characteristics | | | | | |
| t _{d(on)} | Turn-On Delay Time | V - 30 V I - 85 A | | 13 | 35 | ns |
| t _r | Turn-On Rise Time | $V_{DD} = -30 \text{ V}, I_{D} = -8.5 \text{ A},$ $R_{G} = 25 \Omega$ | | 100 | 210 | ns |
| t _{d(off)} | Turn-Off Delay Time | 116 - 20 32 | | 22 | 55 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | | 60 | 130 | ns |
| Qg | Total Gate Charge | V _{DS} = -48 V, I _D = -17 A, | | 21 | 27 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = -10 V | | 4.2 | | nC |
| Q _{gd} | Gate-Drain Charge | (Note 4) | | 10 | | nC |
| Drain-S | ource Diode Characteristics a | nd Maximum Ratings | | | | |
| I _S | Maximum Continuous Drain-Source Did | | | -17 | Α | |
| I _{SM} | Maximum Pulsed Drain-Source Diode F | Forward Current | | | -68 | Α |
| V _{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = -17 \text{ A}$ | | | -4.0 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = -17 A, | | 92 | | ns |
| Q _{rr} | Reverse Recovery Charge $dI_F / dt = 100 \text{ A/}\mu\text{s}$ | | | 0.32 | | μС |

Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 1.2mH, I $_{AS}$ = -17A, V $_{DD}$ = -25V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C 3. $_{SD}$ \leq -17A, di/dt \leq 300A/ $_{HS}$, V $_{DD}$ \leq BV $_{DSS}$, Starting T $_{J}$ = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

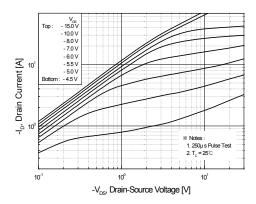


Figure 1. On-Region Characteristics

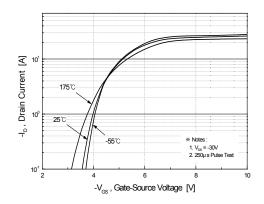


Figure 2. Transfer Characteristics

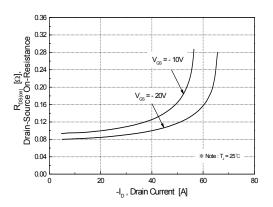


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

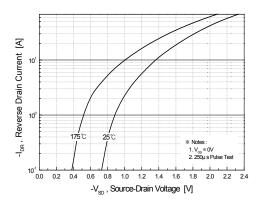


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

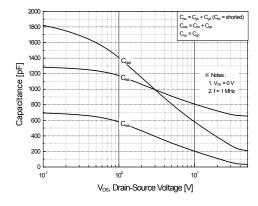


Figure 5. Capacitance Characteristics

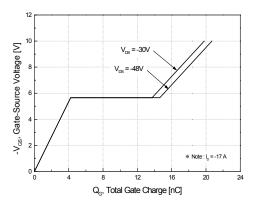
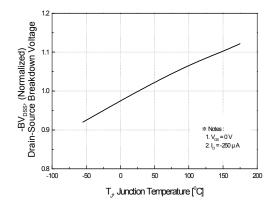


Figure 6. Gate Charge Characteristics

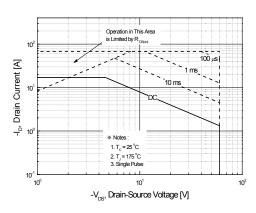
Typical Characteristics (Continued)



25 (Notes: 1.5 (Notes: 1.7 (No

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



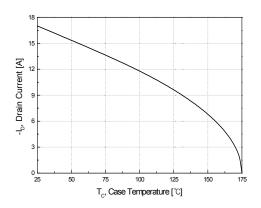


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

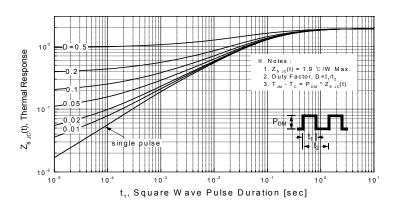
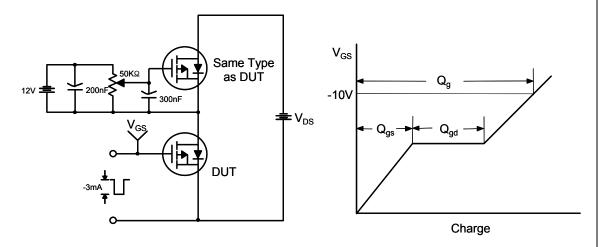
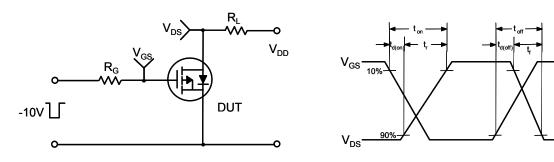


Figure 11. Transient Thermal Response Curve

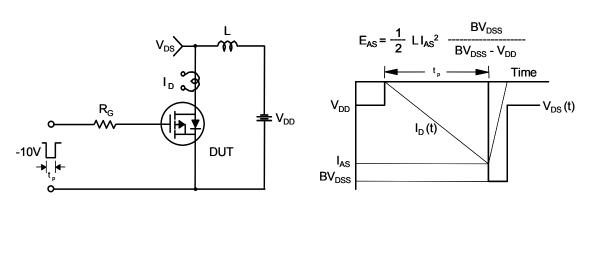
Gate Charge Test Circuit & Waveform



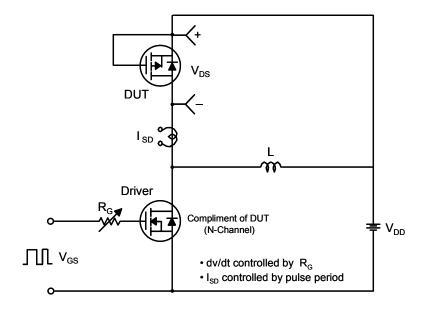
Resistive Switching Test Circuit & Waveforms

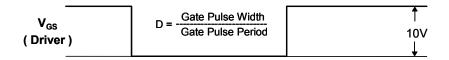


Unclamped Inductive Switching Test Circuit & Waveforms

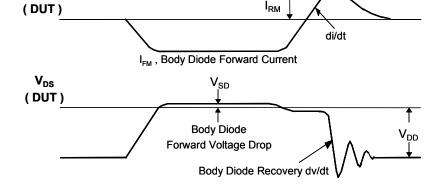


Peak Diode Recovery dv/dt Test Circuit & Waveforms

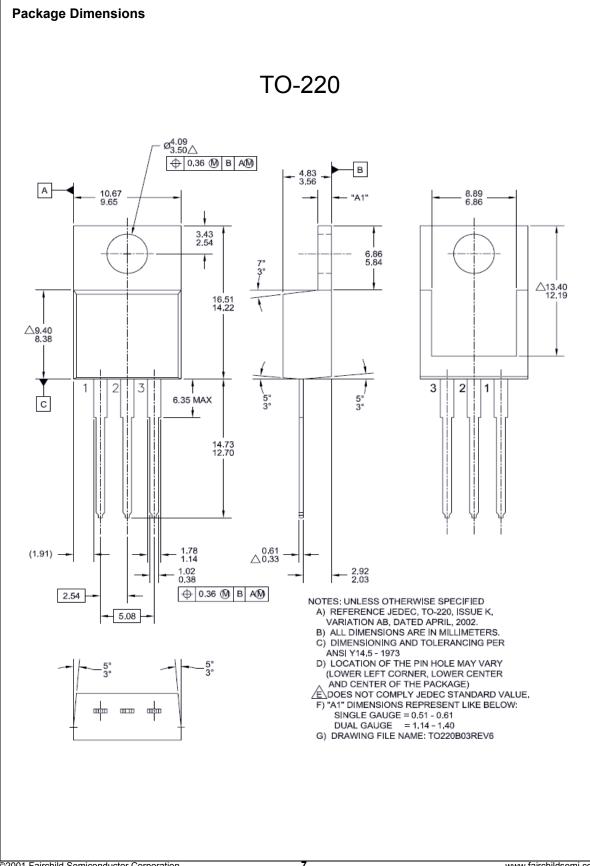




Body Diode Reverse Current



I_{SD}







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